



Attorney's Docket No. 5308-157IP2

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.

Confirmation No.: 3570

Serial No.: 10/045,542

Group Art Unit: 1762

Filed: October 26, 2001

Examiner: Michael. E. Barr

For: METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON
CARBIDE LAYER UTILIZING AN ANNEAL IN A HYDROGEN
ENVIRONMENT

Date: January 20, 2004

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37

C.F.R. § 1.97(b)

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Please find attached a check in the amount of \$180.00 for the fee specified in 37 C.F.R. § 1.17(p). The Commissioner is authorized to charge any additional fee or credit any refund to Deposit Account No. 50-0220.

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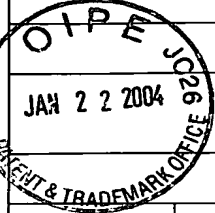
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| FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary) | | | | Attorney Docket Number 5308-1571P2 | | Serial No. 10/045,542 | |
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|  | | | | Applicants: Das et al. | | | |
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| | 7 | WO 98/02924 | 01/22/98 | PCT | | | |
| | 8 | WO 00/13236 | 03/09/00 | PCT | | | |
| OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| | 9 | Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177. | | | | | |
| | 10 | De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152. | | | | | |
| | 11 | Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM. | | | | | |

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